Towards Transport Measurements of Topological Crystalline Insulator Core/Shell GaAs/Pb_{1-x}Sn_xTe Nanowires

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Fabrication of NW devices and I-V characteristics



Conclusions

- Pb_{1-x}Sn_xTe can be grown as full and half shells
 of III-V (GaAs) nanowires in a full composition
 range
- IV-VI shells are constituted from {100} or
 {110} surfaces (with topological protection)
- Possibility to control the topological transition by strain

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- The ohmic contacts to individual NWs have been fabricated by e-beam lithography and Au deposition.
- The best samples exhibit low resistivities

Future plans

- To obtain completely smooth and unbroken Pb_{1-x}Sn_xTe shells on GaAs NWs
- Magnetotransport measurements of individual NW devices
- To grow a second half shell on the chosen sidewalls of NWs
 A way to study TCI hinge states as well as (110) surface
 - A way to study TCI hinge states as well as (110 states of TCI





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